



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SOT23 PNP SILICON PLANAR DARLINGTON TRANSISTORS

BCV26 BCV46

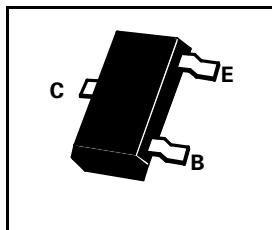
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FEATURES

- * Low saturation voltage

COMPLEMENTARY TYPE – BCV26 - BCV27
BCV46 - BCV47

PARTMARKING DETAILS – BCV26 - ZFD
BCV46 - ZFE



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	BCV26	BCV46	UNIT
Collector-Base Voltage	V_{CBO}	-40	-80	V
Collector-Emitter Voltage	V_{CEO}	-30	-60	V
Emitter-Base Voltage	V_{EBO}	-10		V
Peak Pulse Current	I_{CM}	-800		mA
Continuous Collector Current	I_C	-500		mA
Base Current	I_B	-100		mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330		mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150		$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	BCV26		BCV46		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40		-80		V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-30		-60		V	$I_C=10mA$ *
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-10		-10		V	$I_E=10\mu A$
Collector Cut-Off Current	I_{CBO}		-100		-100	nA nA μA μA	$V_{CB} = -30V$ $V_{CB} = -60V$ $V_{CB} = -30V, T_{amb} = 150^{\circ}C$ $V_{CB} = -60V, T_{amb} = 150^{\circ}C$
Emitter Base Cut-Off Current	I_{EBO}		-100		-100	nA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-1.0		-1.0	V	$I_C = 100mA, I_B = -0.1mA$ *
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.5		-1.5	V	$I_C = 100mA, I_B = -0.1mA$ *
Static Forward Current Transfer Ratio	h_{FE}	4K 10K 20K 4K		2K 4K 10K 2K			$I_C = 100\mu A, V_{CE} = -1V \dagger$ $I_C = 10mA, V_{CE} = -5V$ * $I_C = 100mA, V_{CE} = -5V$ * $I_C = 500mA, V_{CE} = -5V$ *
Transition Frequency	f_T	200 Typical		200 Typical		MHz	$I_C = 50mA, V_{CE} = -5V$ $f = 20MHz$
Output Capacitance	C_{obo}	4.5 Typical		4.5 Typical		pF	$V_{CB} = -10V, f = 1MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

Spice parameter data is available upon request for these devices † Periodic Sample Test Only.